| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|---|---|---|---|---|---|---|
| L1 | 23918 | spacer near2 (second! another addition$4) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/01/21 15:35 |
| L2 | 372364 | si?n? or "si.sub.3 or n.sub.4" or nitride | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/01/21 15:03 |
| L3 | 5351 | spacer near2 2 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/01/21 15:55 |
| L4 | 64 | (dry plasma pe) near2 etch$4 near2 3 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/01/21 15:54 |
| L5 | 205622 | mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/01/21 15:06 |
| L6 | 33 | 4 and 5 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/01/21 15:06 |
| L7 | 32 | 6 and (@ad < "20040227") | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/01/21 15:59 |
| L14 | 2 | "20030235966".pn. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/01/21 15:24 |
| L15 | 105710 | (dry plasma pe) near2 etch$4 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/01/21 15:25 |
| L16 | 1 | 14 and 15 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/01/21 15:25 |

| L17 | 2237 | (dry plasma pe) near2 etch$4 near2 2 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/01/21 15:35 |
|---|---|---|---|---|---|---|
| L18 | 279 | 17 and 3 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/01/21 15:35 |
| L19 | 117 | 17 and 3 and 1 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/01/21 15:35 |
| L20 | 638 | 1 near4 2 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/01/21 15:36 |
| L21 | 48 | 20 and 17 and 1 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/01/21 15:36 |
| L22 | 46 | 21 and (@ad < "20040227") | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/01/21 15:36 |
| L23 | 2237 | (dry plasma pe) near2 etch$4 near2 2 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/01/21 15:54 |
| L24 | 131 | 3 and 23 and 5 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/01/21 15:54 |
| L25 | 129 | 24 and (@ad < "20040227") | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/01/21 15:54 |
| L26 | 3900081 | remov$4 (spacer 2) near4 (plasma dry pe rie) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/01/21 15:57 |

| L27 | 4596 | 26 and 3 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/01/21 15:56 |
|------|---------|-----------------------------------------------------|----------------------------------------------------|----|-----|------------------|
| L28 | 3896307 | remov$4 (spacer near2 2) near4 (plasma dry pe rie) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/01/21 15:56 |
| L29 | 2460 | remov$4 near4 (spacer 2) near4 (plasma dry pe rie) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/01/21 15:57 |
| L30 | 380 | 29 and 3 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/01/21 15:57 |
| L31 | 2445131 | (wet acid hf hydrofluor$6 hydro adj fluor$6 hydro-fluor$4) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/01/21 15:57 |
| L32 | 1459063 | sio? or "sio.sub.2" or oxide | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/01/21 15:58 |
| L33 | 45048 | 31 near2 32 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/01/21 15:59 |
| L34 | 57 | 30 and 33 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/01/21 15:59 |
| L35 | 55 | 34 and (@ad < "20040227") | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/01/21 16:00 |
| L36 | 4974 | ((438/303) or (438/305) or (438/595) or (438/710) or (438/756)).CCLS. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/01/21 16:41 |

| S95 | 201409 | mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/01/21 15:06 |
|---|---|---|---|---|---|---|
| S96 | 23390 | spacer near2 (second! another addition$4) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/01/21 15:03 |
| S97 | 4 | (S95 and S96).ti. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/11/29 15:56 |
| S98 | 234 | (S95 and S96).ab. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/11/29 15:56 |
| S99 | 30122 | spacer near2 (second! another addition$4 outer) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/01/19 18:24 |
| S100 | 3860 | (dry or plasma) near2 etch$4 near2 (second! another addition$4 outer) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/01/19 18:39 |
| S101 | 3861 | (dry plasma pe) near2 etch$4 near2 (second! another addition$4 outer) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/01/21 15:05 |
| S102 | 2115 | (wet acid hf hydrofluor$6 hydro adj fluor$6 hydro-fluor$4) near2 etch$4 near2 (second! another addition$4 outer) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/01/19 18:39 |
| S103 | 24 | S99 and S101 and S102 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/01/19 18:38 |
| S104 | 1275 | S99 near4 (remov$4 ) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/01/21 11:34 |

| S105 | 105550 | (dry or plasma) near2 etch$4 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/01/19 18:39 |
|------|---------|------------------------------|---------|----|----|-----------|
| S106 | 71848 | (wet acid hf hydrofluor$6 hydro adj fluor$6 hydro-fluor$4) near2 etch$4 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | ·2005/01/21 15:57 |
| S107 | 259 | S105 and S106 and S104 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/01/19 18:40 |
| S108 | 253 | S107 and (@ad < "20040227") | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/01/21 15:07 |
| S109 | 1458111 | sio? or "sio.sub.2" or oxide | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/01/21 15:58 |
| S110 | 26552 | conformal$4 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/01/21 11:30 |
| S111 | 17781 | spacer near4 (remov$4 ) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/01/21 11:34 |
| S112 | 205372 | mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/01/21 11:36 |
| S113 | 998 | S112 and S110 and S111 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/01/21 11:37 |
| S114 | 105586 | (dry plasma pe) near2 etch$4 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/01/21 11:36 |

| S11 5 | 2465 | S112 and S110 and S114 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/01/21 11:36 |
|---|---|---|---|---|---|---|
| S11 6 | 159 | S112 and S110 and S111 same S114 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/01/21 11:37 |